

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

Waclaw C. Koscielniak

Application No.: NEW

Filed: HEREWITH

For: DMOS TRANSISTOR STRUCTURE  
WITH GATE ELECTRODE TRENCH  
FOR HIGH DENSITY INTEGRATION  
AND METHOD OF FABRICATING  
THE STRUCTURE

Group Art Unit: Unknown

Examiner: Unknown

**PRELIMINARY AMENDMENT**

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San Francisco, CA 94105  
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M/S Patent Application  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**CERTIFICATE OF MAILING**

I hereby certify that this correspondence is being deposited  
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22313-1450 on December 1, 2003.

STALLMAN & POLLOCK LLP

Dated: 12/1/03

By: 

Janet Chan

Sir:

It is requested that the above-identified application be amended as follows:

**Amendments to the Specification** begin on page 2 of this paper.

**Amendment to the Claims** are reflected in the listing of claims which begins on page 3 of this paper.